





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
221	25mΩ @ V _{GS} = 10V	6.2A
30V	$28m\Omega$ @ V _{GS} = 4.5V	5.8A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN3028LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Load Switch
- DC-DC Converters
- Power Management Functions

Mechanical Data

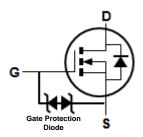
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208⁽³⁾
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



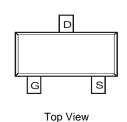


SOT23

Top View







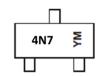
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3028LQ-7	SOT23	3,000/Tape & Reel
DMN3028LQ-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



4N7 = Product Type Marking Code Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	Н		J	K	L	М	N	0	Р	R	S
	•											
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	30	V
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current (Note 6) Vgs = 10V	lo	6.2 4.9	А		
Pulsed Drain Current (380µs Pulse, Duty Cycle = 19	I _{DM}	40	Α		
Maximum Body Diode Forward Current (Note 6)			Is	2	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.86	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	146	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	88	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	13	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current	IDSS		1	1	μΑ	V _{DS} = 24V, V _{GS} = 0V		
Gate-Body Leakage	I _{GSS}		1	±10	μΑ	$V_{GS} = \pm 16V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.8	1	1.8	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
Static Drain-Source On-Resistance	RDS(ON)	111	16 19 47	25 28 68	mΩ	VGS = 10V, ID = 4.0A VGS = 4.5V, ID = 3.5A VGS = 2.5V, ID = 2.5A		
Source-Drain Diode Forward Voltage	V _{SD}		0.7	1.2	V	Vgs = 0V, Is = 1A		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	_	680	_	pF			
Output Capacitance	Coss		96	1	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz		
Reverse Transfer Capacitance	Crss		74	1	pF	1 - 1.61/11 12		
Gate Resistance	Rg		1.7	1	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge (Vgs = 10V)	Qg		10.9	1	nC			
Total Gate Charge (V _{GS} = 4.5V)	Qg		7.8	1	nC	V _{DS} = 15V, I _D = 4A		
Gate-Source Charge	Qgs		1.6	1	nC	VDS = 13V, ID = 4A		
Gate-Drain Charge	Q_{gd}		4.8	1	nC			
Turn-On Delay Time	td(ON)	_	6.7	_	ns			
Turn-On Rise Time	t _R		1.5		ns	$V_{DD} = 15V, V_{GS} = 10V,$		
Turn-Off Delay Time	tD(OFF)	_	17.5	_	ns	$R_L = 15\Omega$, $R_G = 6\Omega$		
Turn-Off Fall Time	t _F	_	10.4	_	ns			

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

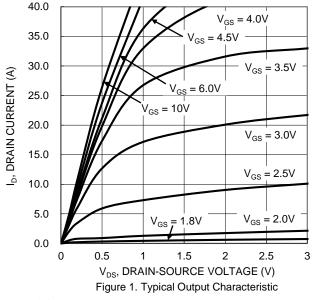
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.







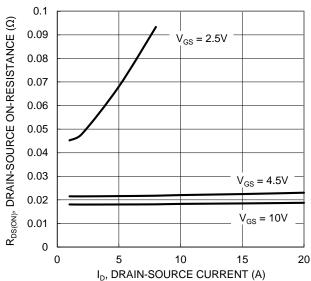


Figure 3. Typical On-Resistance vs. Drain Current

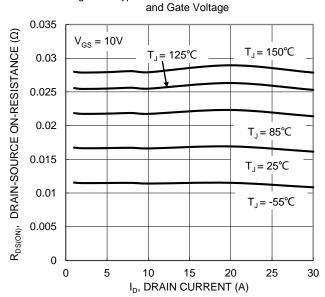
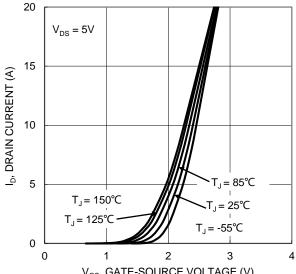


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

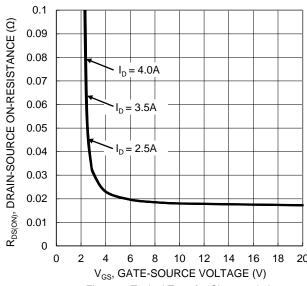


Figure 4. Typical Transfer Characteristic

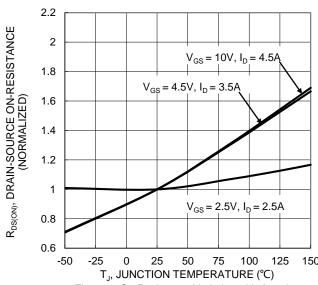


Figure 6. On-Resistance Variation with Junction Temperature





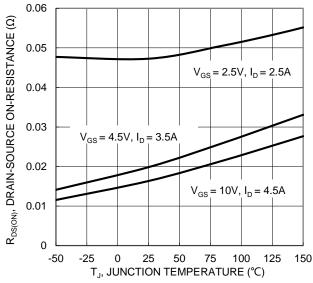


Figure 7. On-Resistance Variation with Junction Temperature

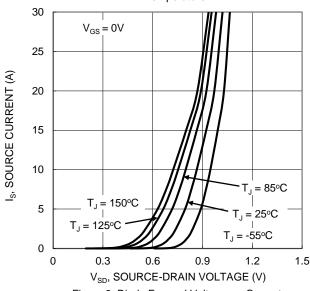


Figure 9. Diode Forward Voltage vs. Current

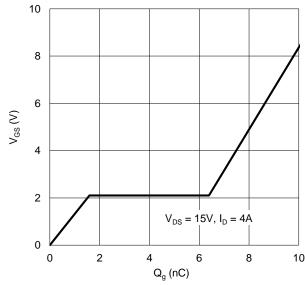


Figure 11. Gate Charge

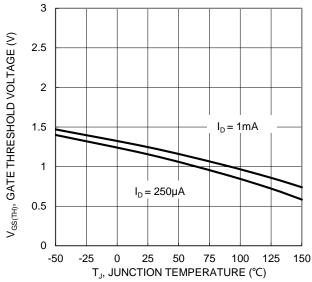


Figure 8. Gate Threshold Variation vs. Junction Temperature

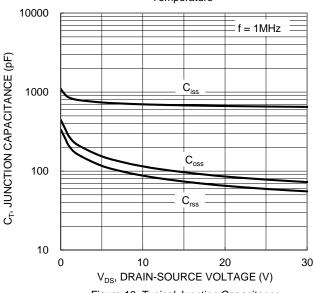


Figure 10. Typical Junction Capacitance

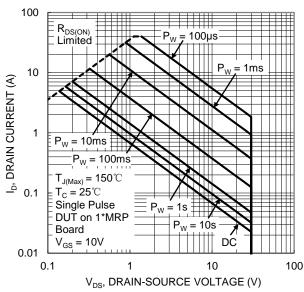


Figure 12. SOA, Safe Operation Area



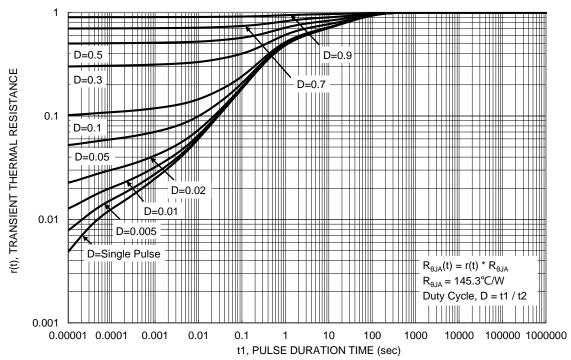


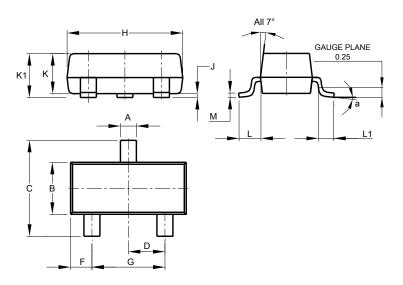
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

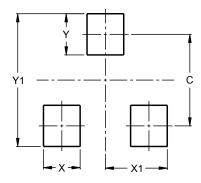


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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